

BSS63LT1G, NSVBSS63LT1G

High Voltage Transistor

PNP Silicon

Features

- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	-100	Vdc
Collector-Emitter Voltage $R_{BE} = 10\text{ k}\Omega$	V_{CER}	-110	Vdc
Collector Current - Continuous	I_C	-100	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (Note 1) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

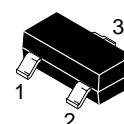
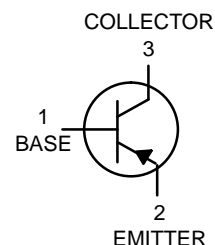
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-5 = 1.0 x 0.75 x 0.062 in.
2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.



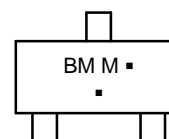
ON Semiconductor®

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SOT-23
CASE 318
STYLE 6

MARKING DIAGRAM



BM = Device Code
M = Date Code*
■ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
BSS63LT1G	SOT-23 (Pb-free)	3000 / Tape & Reel
NSVBSS63LT1G	SOT-23 (Pb-free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage ($I_C = -100\ \mu\text{Adc}$)	$V_{(BR)CEO}$	-100	-	-	Vdc
Collector–Emitter Breakdown Voltage ($I_C = -10\ \mu\text{Adc}$, $I_E = 0$, $R_{BE} = 10\ \text{k}\Omega$)	$V_{(BR)CER}$	-110	-	-	Vdc
Collector–Base Breakdown Voltage ($I_E = -10\ \mu\text{Adc}$, $I_C = 0$)	$V_{(BR)CBO}$	-110	-	-	Vdc
Emitter–Base Breakdown Voltage ($I_E = -10\ \mu\text{Adc}$)	$V_{(BR)EBO}$	-6.0	-	-	Vdc
Collector Cutoff Current ($V_{CB} = -90\ \text{Vdc}$, $I_E = 0$)	I_{CBO}	-	-	-100	nAdc
Collector Cutoff Current ($V_{CE} = -110\ \text{Vdc}$, $R_{BE} = 10\ \text{k}\Omega$)	I_{CER}	-	-	-10	μAdc
Emitter Cutoff Current ($V_{EB} = -6.0\ \text{Vdc}$, $I_C = 0$)	I_{EBO}	-	-	-200	nAdc

ON CHARACTERISTICS

DC Current Gain ($I_C = -10\ \text{mAdc}$, $V_{CE} = -1.0\ \text{Vdc}$) ($I_C = -25\ \text{mAdc}$, $V_{CE} = -1.0\ \text{Vdc}$)	h_{FE}	30 30	- -	- -	-
Collector–Emitter Saturation Voltage ($I_C = -25\ \text{mAdc}$, $I_B = -2.5\ \text{mAdc}$)	$V_{CE(sat)}$	-	-	-250	mVdc
Base–Emitter Saturation Voltage ($I_C = -25\ \text{mAdc}$, $I_B = -2.5\ \text{mAdc}$)	$V_{BE(sat)}$	-	-	-900	mVdc

SMALL–SIGNAL CHARACTERISTICS

Current–Gain–Bandwidth Product ($I_C = -25\ \text{mAdc}$, $V_{CE} = -5.0\ \text{Vdc}$, $f = 20\ \text{MHz}$)	f_T	50	95	-	MHz
Case Capacitance ($I_E = I_C = 0$, $V_{CB} = -10\ \text{Vdc}$, $f = 1.0\ \text{MHz}$)	C_C	-	-	20	pF
Noise Figure ($I_C = -0.2\ \text{mA}$, $V_{CE} = -5.0\ \text{Vdc}$, $R_g = 2\ \text{k}\Omega$, $f = 1.0\ \text{kHz}$, $BW = 200\ \text{Hz}$)	NF	-	-	10	dB

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- FR-5 = $1.0 \times 0.75 \times 0.062$ in.
- Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.

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TYPICAL CHARACTERISTICS

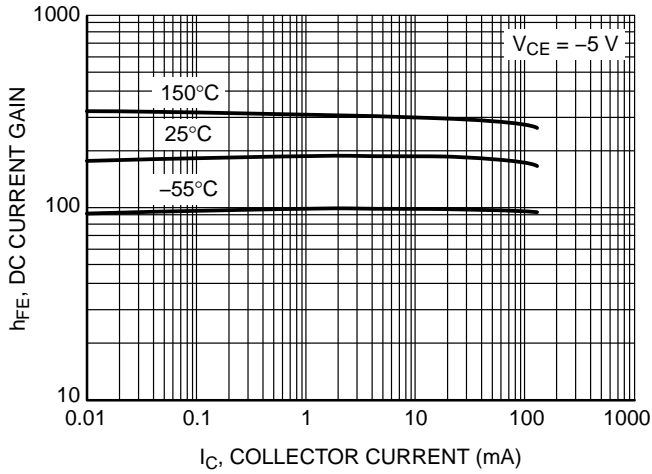


Figure 1. DC Current Gain

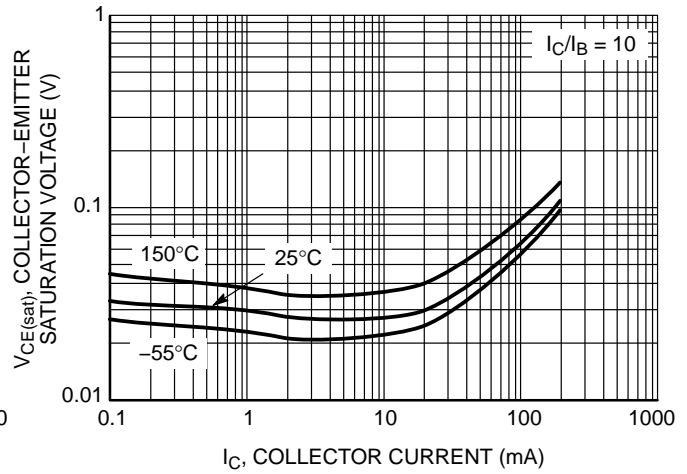


Figure 2. Collector-Emitter Saturation Voltage vs. Collector Current

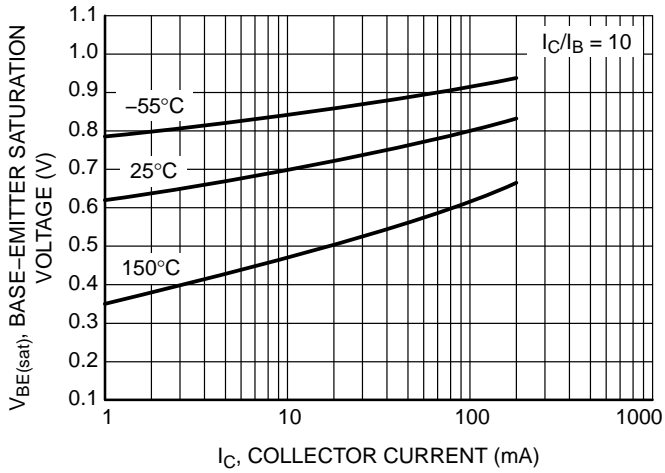


Figure 3. Base-Emitter Saturation Voltage vs. Collector Current

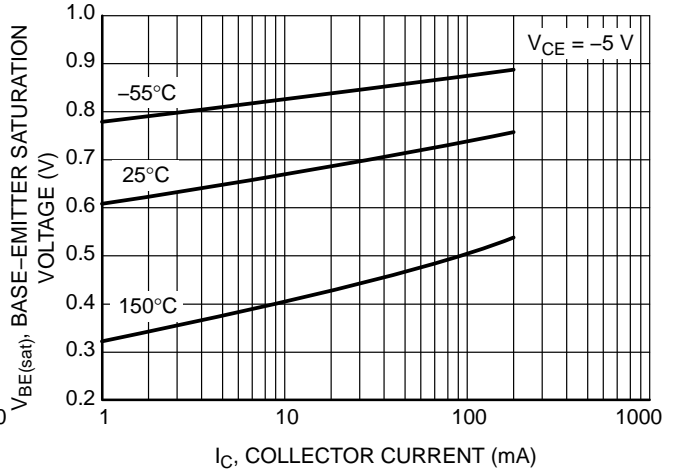


Figure 4. Base-Emitter Voltage vs. Collector Current

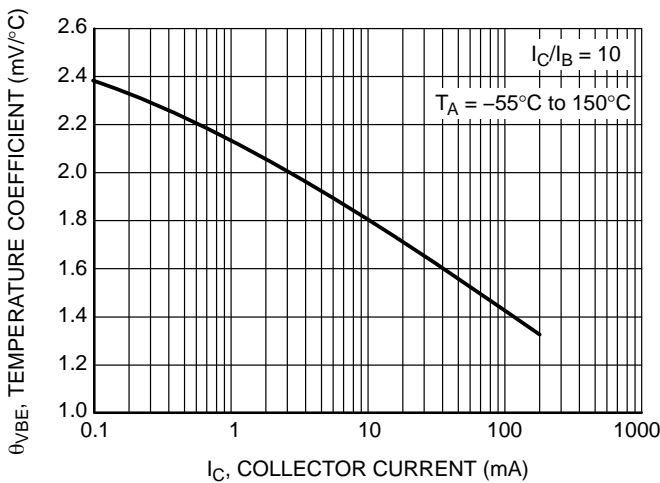


Figure 5. Base-Emitter Temperature Coefficient

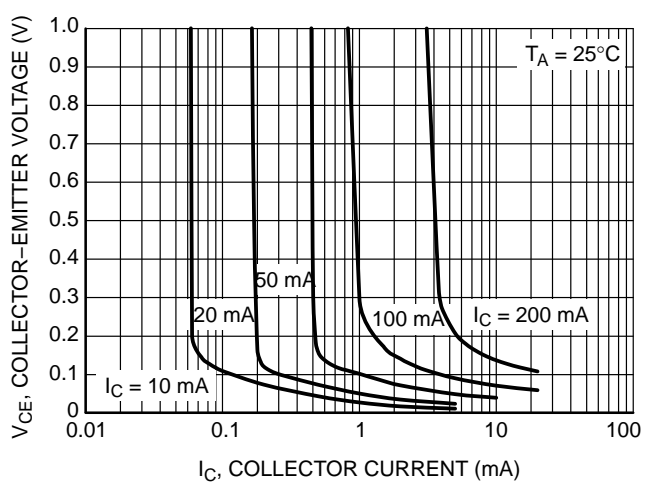


Figure 6. Collector Saturation Region

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TYPICAL CHARACTERISTICS

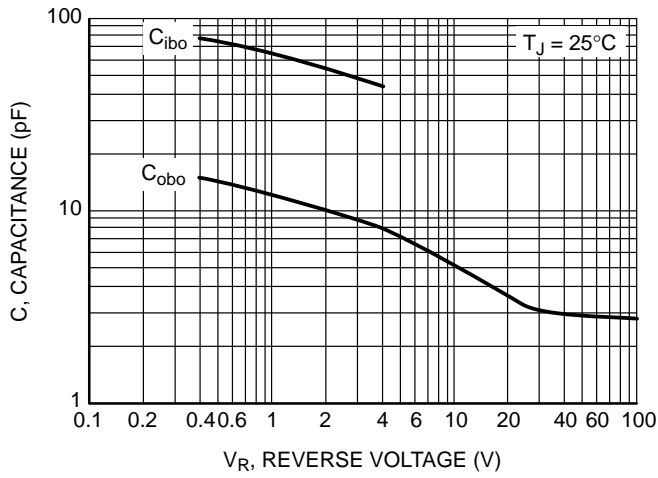


Figure 7. Capacitance

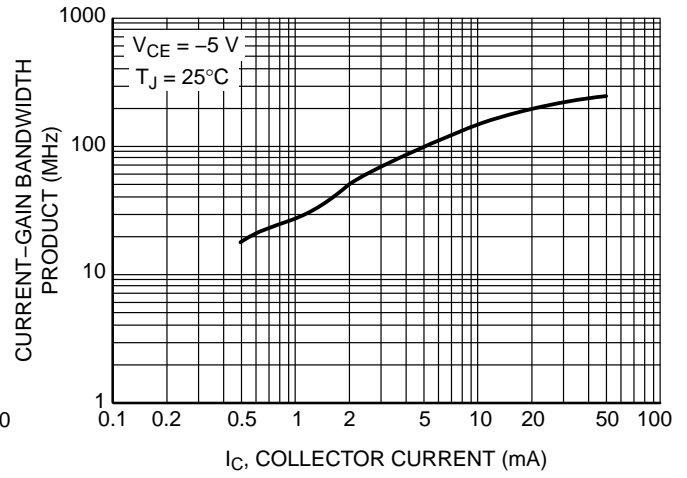


Figure 8. Current-Gain Bandwidth Product

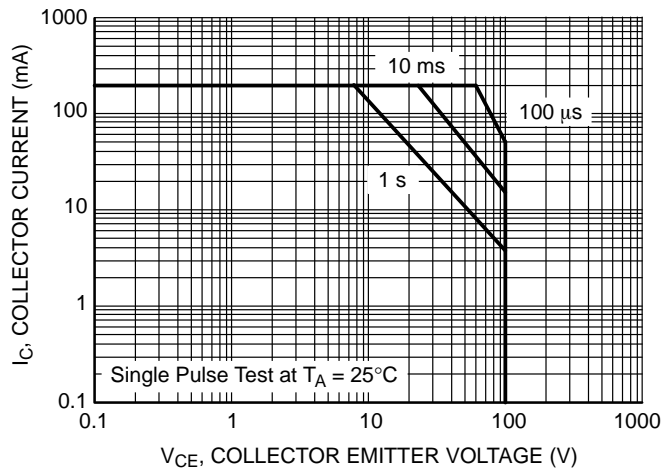
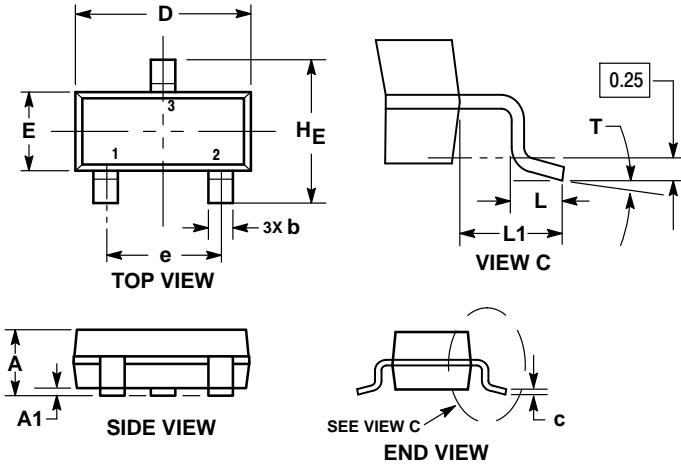


Figure 9. Safe Operating Area

BSS63LT1G, NSVBSS63LT1G

PACKAGE DIMENSIONS

SOT-23 (TO-236)
CASE 318-08
ISSUE AR



NOTES:

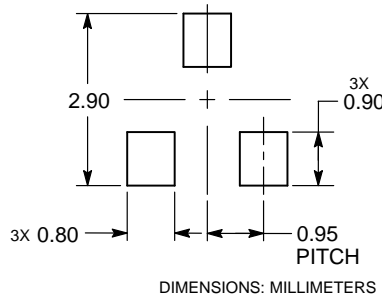
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	—	10°	0°	—	10°

STYLE 6:

1. BASE
2. EMITTER
3. COLLECTOR

RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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